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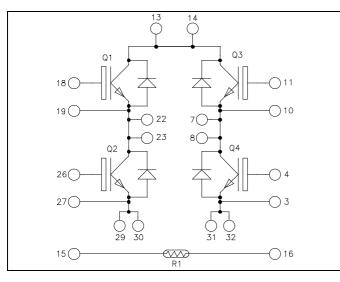
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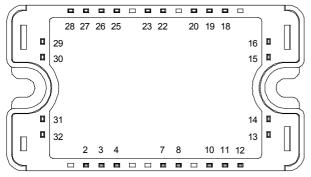
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Full - Bridge NPT IGBT Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

$V_{CES} = 1200V$ $I_{C} = 25A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Symmetrical design
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive T_C of V_{CEsat}
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	40	
I _C	Continuous Conector Current	$T_C = 80^{\circ}C$	25	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V_{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	208	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 125^{\circ}C$	50A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_j = 25^{\circ}C$			250	μA
I _{CES}	Zero Gate voltage Concetor Current	$V_{CE} = 1200V$	$T_j = 125^{\circ}C$			500	μΑ
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	2.5	3.2	3.7	V
V _{CE(sat)}	Conector Ennitier Saturation Voltage	$I_C = 25A$	$T_j = 125^{\circ}C$		4.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1 \text{mA}$		4		6	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			1650		
C _{oes}	Output Capacitance				250		pF
C _{res}	Reverse Transfer Capacitance	f = 1MHz			110		
Qg	Total gate Charge	$V_{GE} = 15V$			160		nC
Q _{ge}	Gate – Emitter Charge	$V_{Bus} = 600V$			10		
Q _{gc}	Gate – Collector Charge	$I_{\rm C}=25{\rm A}$			70		
T _{d(on)}	Turn-on Delay Time	Inductive Switch		60			
Tr	Rise Time	$V_{GE} = 15V$			50		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 25A$		305		ns	
$T_{\rm f}$	Fall Time	$R_G = 22\Omega$		30			
T _{d(on)}	Turn-on Delay Time	Inductive Switch	ning (125°C)		60		
Tr	Rise Time	$V_{GE} = 15V$			50		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 25A$ $R_{G} = 22\Omega$			346		ns
T _f	Fall Time				40		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		3.5		T.
E _{off}	Turn-off Switching Energy	$I_{C} = 25A$ $R_{G} = 22\Omega$	$T_j = 125^{\circ}C$		1.5		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V	
I _{RM}	Maximum Davanaa Laakaga Current	V _R =1200V	$T_j = 25^{\circ}C$			100	۸	
IRM	Maximum Reverse Leakage Current	v _R -1200v	$T_{j} = 125^{\circ}C$			250	μA	
$I_{\rm F}$	Forward Current		$Tc = 80^{\circ}C$		25		А	
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 25 A$ $V_{\rm GE} = 0 V$	$T_i = 25^{\circ}C$		2.1		V	
▼ F			$T_i = 125^{\circ}C$		1.9		•	
t	t _{rr} Reverse Recovery Time		$T_j = 25^{\circ}C$		95		ns	
ι _{rr}		$T_j = 125^{\circ}C$		190		115		
Q _{rr}	Pavaraa Paaayary Charga		$I_{\rm F} = 25 \text{A}$ $V_{\rm P} = 600 \text{V}$	$T_j = 25^{\circ}C$		2.1		μC
Qrr	Reverse Recovery charge	$di/dt = 1000 A/\mu s$	$T_{j} = 125^{\circ}C$		4.5		μΟ	
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		0.75		mJ	
Ľ	Reverse Recovery Energy		$T_{j} = 125^{\circ}C$		1.5		1113	



Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

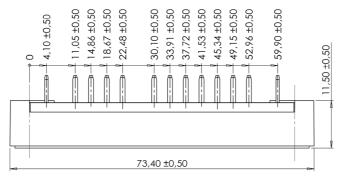
Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		Κ
-	Rec. To Thermister termereture				

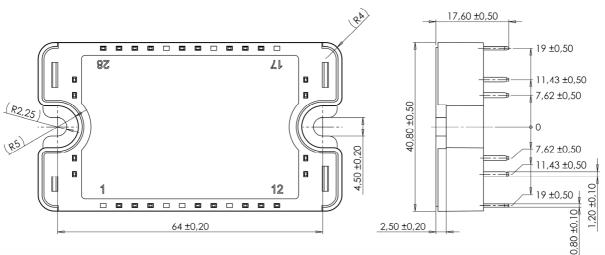
 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$ T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance IGBT Diode				0.6	°C/W	
R _{th} JC			Diode			1.2	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range -40 150						
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature					100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

SP3 Package outline (dimensions in mm)





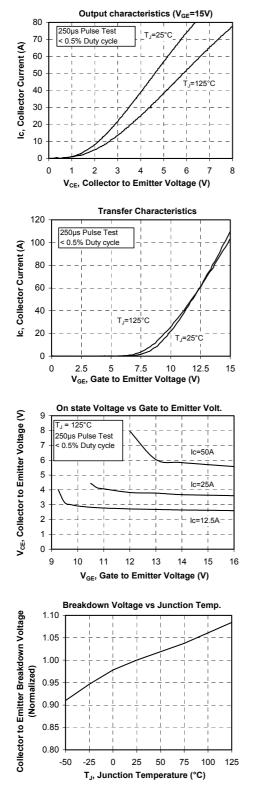
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

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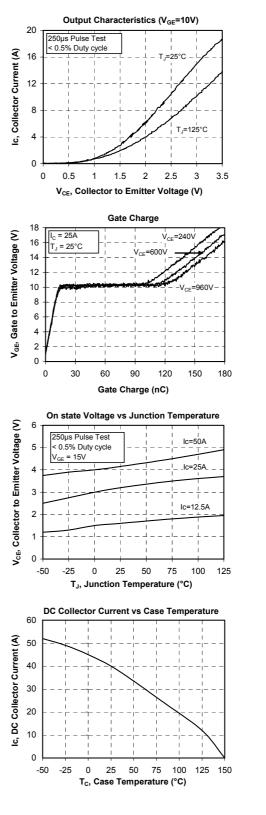
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Typical Performance Curve



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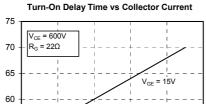


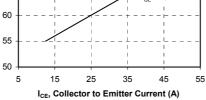
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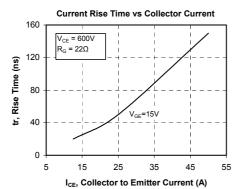
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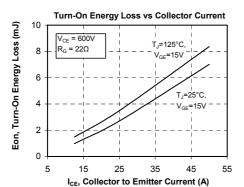


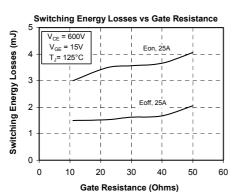
td(on), Turn-On Delay Time (ns)



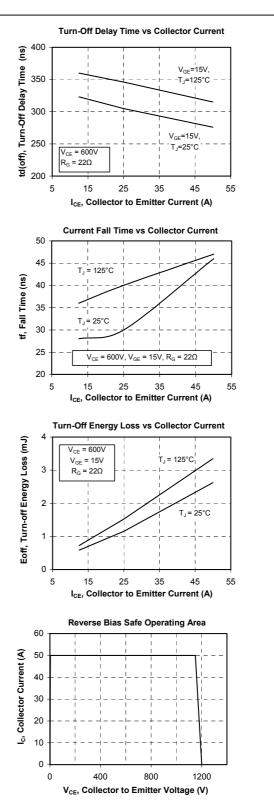








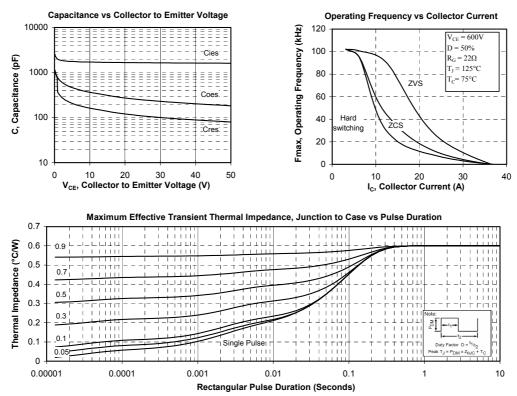
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